



# VEERMATA JIJABAI TECHNOLOGICAL INSTITUTE

[Central Technological Institute, Maharashtra State]

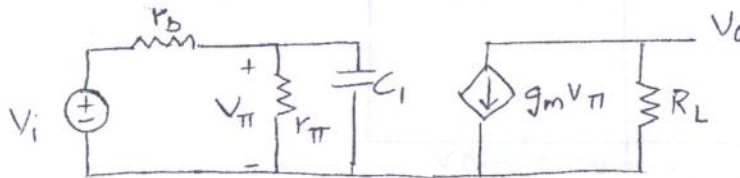
Matunga, Mumbai-400 019

SEMESTER EXAMINATION *May 2012*  
SEMESTER & PROGRAM *IV SYBTech*  
*EC/EXTC*  
TIME ALLOWED *3 HRS.*  
COURSE (CourseCode) : *ECAD II*

DATE OF EXAM *21/05/2012*  
TIME *1.30 - 4.30 pm*  
MARKS *100*

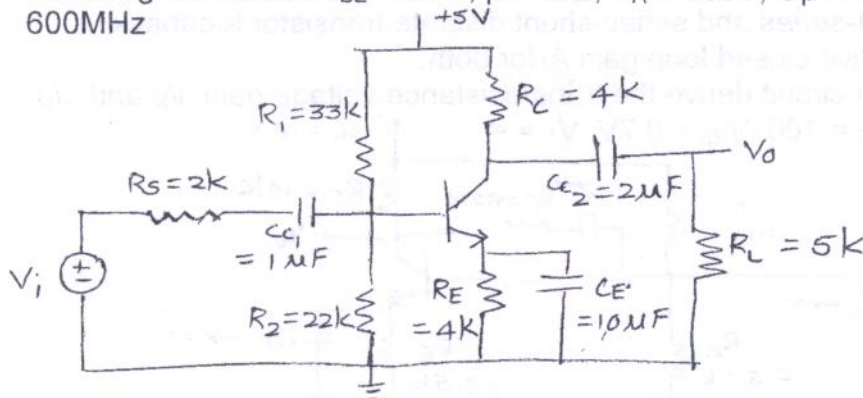
- Instructions:**
1. Attempt All questions.
  2. **Figures** to the right indicate **Full Marks**.
  3. Assume suitable **additional data**, if required.
  4. Illustrate your answer with neat sketches whenever necessary.

Q1. a) For the hybrid -  $\pi$  equivalent circuit given below: 10



- i) Derive the expression for the voltage gain transfer function
- ii) If the transistor is biased at  $I_{CQ} = 1 \text{ mA}$  and if  $R_L = 4 \text{ k}\Omega$  and  $\beta_o = 100$  determine the midband voltage gain for a)  $r_b = 100 \Omega$  and b)  $r_b = 500 \Omega$
- iii) For  $C_1 = 2.2 \text{ pF}$ , determine the -3dB frequency for the two above values of  $r_b$

b) For the given circuit  $V_{BE} = 0.7 \text{ V}$ ,  $\beta = 120$ ,  $V_A = 100 \text{ V}$ ,  $C_\mu = 1 \text{ pF}$ , and  $f_T = 600 \text{ MHz}$  10

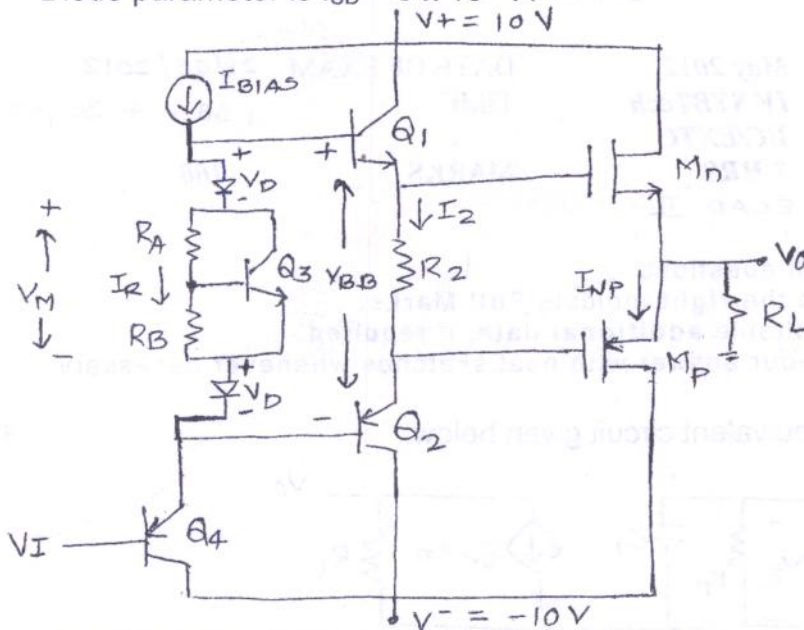


- i) Determine  $C_\pi$  and the equivalent Miller Capacitance  $C_M$ . State any approximations or assumptions that you make.
- ii) Find the upper 3 dB frequency and the midband voltage gain

Q2. Design the output stage configuration below. The current  $I_{BIAS}$  is 5mA and the zero output quiescent current in  $M_n$  and  $M_p$  is to be 0.5 mA. MOSFET parameters are  $V_{TN} = 0.8 \text{ V}$ ,  $V_{TP} = -0.8 \text{ V}$ ,  $K_n = K_p = 5 \text{ mA/V}^2$  and  $\lambda = 0$ . BJT parameters are  $I_{S1} = I_{S2} = 10^{-12} \text{ A}$ ,  $I_{S3} = I_{S4} = 2 \times 10^{-13} \text{ A}$ ,  $\beta = 150$  20

P.T.O

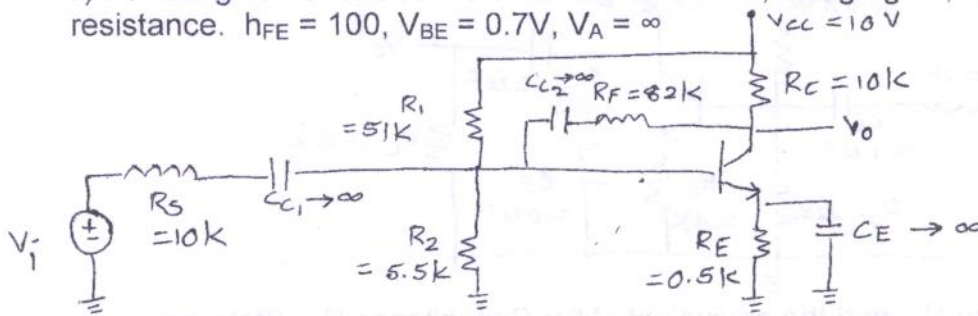
Diode parameter is  $I_{SD} = 5 \times 10^{-13} \text{ A}$



Also Given  $I_2 = 2 \text{ mA}$ ,  $I_{C3} = 0.9 I_{BIAS}$  and  $I_R = 0.1 I_{BIAS}$   
 Find  $V_{GSP}$ ,  $V_{GSP}$ ,  $R_2$ ,  $V_{BE1}$ ,  $V_{BE2}$ ,  $V_{BB}$ ,  $V_D$ ,  $V_M$ ,  $V_{BE3}$ ,  $R_B$ ,  $R_A$ ,  $V_{EB4}$ ,  $V_I$

- Q3. a) Derive the normalized DC transfer characteristics for BJT diffamp. **05**  
 b) Determine the maximum differential mode input signal that can be applied and still maintain linearity in the differential amplifier. **05**  
 c) Discuss Diff-Amp Frequency Response due to Differential-Mode Input Signal and Common-Mode Input Signal in detail **10**

- Q4. a) i) Explain shunt-series and series-shunt discrete transistor feedback topologies. Derive closed loop gain  $A_f$  for both. **06**  
 ii) For the given circuit derive the transresistance, voltage gain, i/p and o/p resistance.  $h_{FE} = 100$ ,  $V_{BE} = 0.7 \text{ V}$ ,  $V_A = \infty$  **10**



- b) Explain with the help of an example the approach to derive the loop gain of discrete transistor circuits **04**

- Q5. a) Explain the Barkhausen Criterion and working of the Phase-Shift Oscillator in detail **08**  
 b) For one sided output derive CMRR for MOSFET diffamp **08**  
 c) Explain inductively coupled power amplifier with circuit diagram and load line. **04**